

Description

The TFS080N04N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other switching application.

General Feature

$V_{DS} = 30V$, $I_D = 30A$

$R_{DS(ON) Typ} = 8.5m\Omega @ V_{GS}=10V$

$R_{DS(ON) Typ} = 12m\Omega @ V_{GS}=4.5V$

High Power and current handling capability

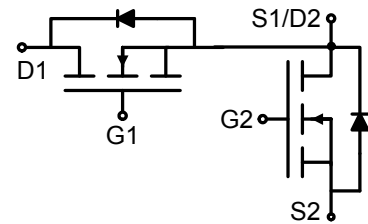
Lead free product is acquired

Surface mount package

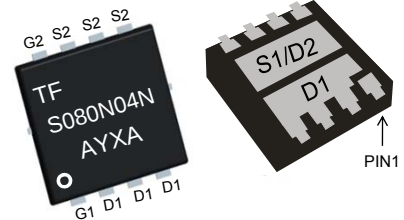
Application

Battery switch

DC/DC converter



Schematic diagram



DFN5060-8L

●Package Marking and Ordering Information:

Part NO.	TFS080N04N
Marking1	S080N04N: TFS080N04N
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit (pcs)	5000

●Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	30	A
	$I_{D@TC=75^\circ C}$	21	A
	$I_{D@TC=100^\circ C}$	18	A
Pulsed Drain Current ^①	I_{DM}	90	A
Total Power Dissipation	$P_{D@TC=25^\circ C}$	30	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	1.5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	80	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	6.0	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	65	° C/W
Soldering temperature, wavesoldering for 8 s	T_{sold}	-	-	265	° C

●Electronic Characteristics($T_j=25$,unless otherwise notse)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.3	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	8.5	9.5	m Ω
		$V_{GS}=4.5V, I_D=10A$	-	12	16	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=15A$	-	18	-	S
Source-drain voltage	V_{SD}	$I_S=15A$	-	-	1.20	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz $V_{DS}=20V$ $V_{GS}=0V$	-	1235	-	pF
Output capacitance	C_{oss}		-	152.5	-	
Reverse transfer capacitance	C_{rss}		-	138.0	-	

●Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 20V$	-	25.5	-	nC
Gate - Source charge	Q_{gs}	$I_D = 20A$	-	3.20	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	6.50	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Typical Electrical and Thermal Characteristics

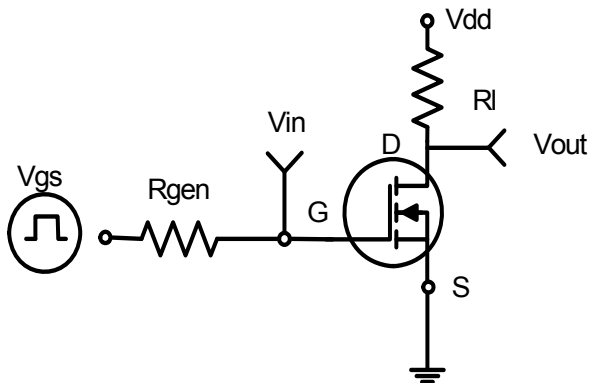


Figure 1 Switching Test Circuit

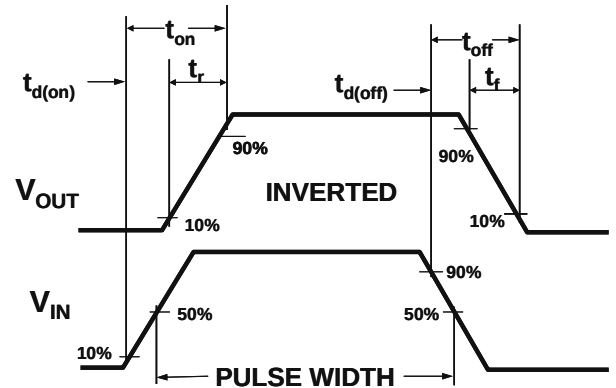


Figure 2 Switching Waveforms

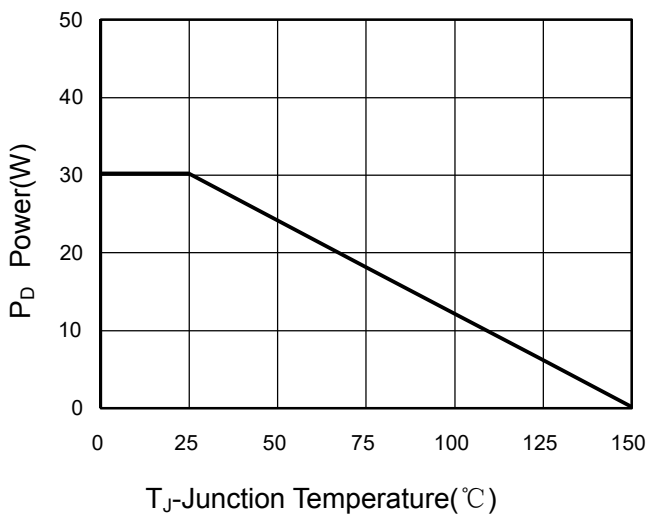


Figure 3 Power Dissipation

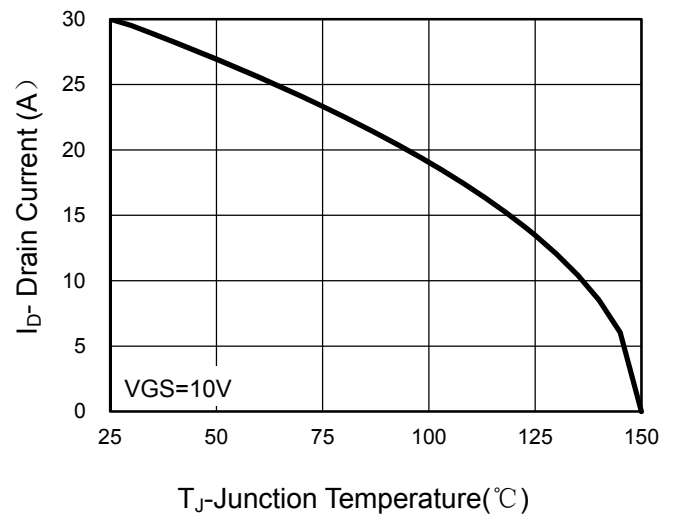


Figure 4 Drain Current

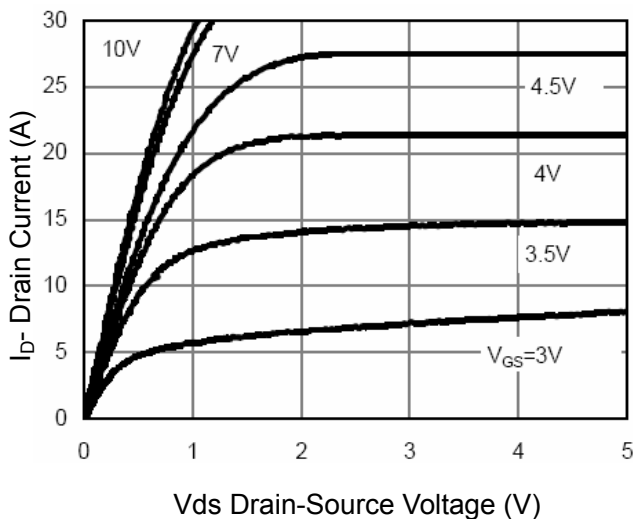


Figure 5 Output Characteristics

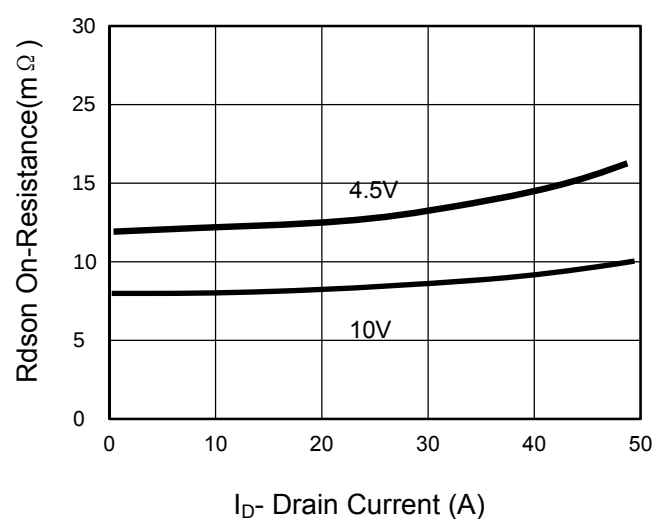


Figure 6 Drain-Source On-Resistance

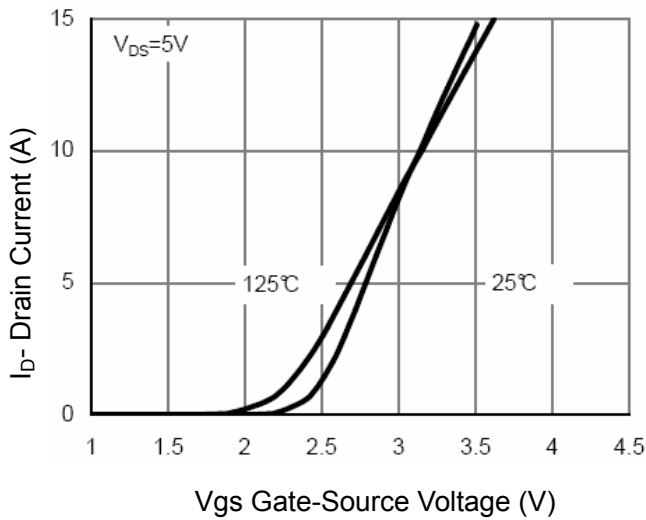


Figure 7 Transfer Characteristics

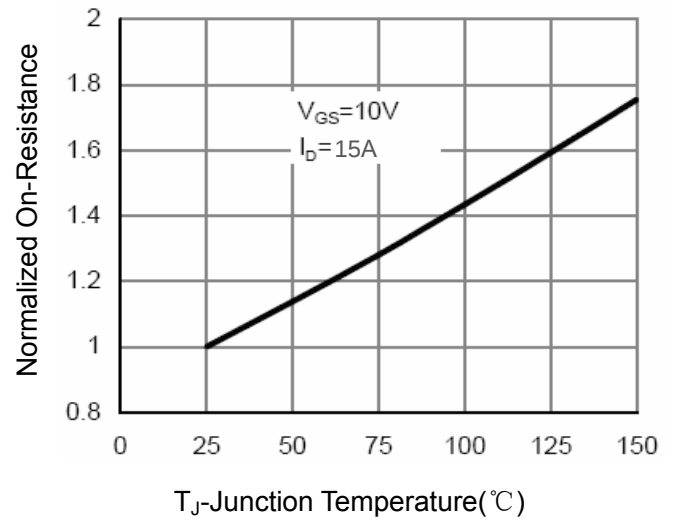


Figure 8 Drain-Source On-Resistance

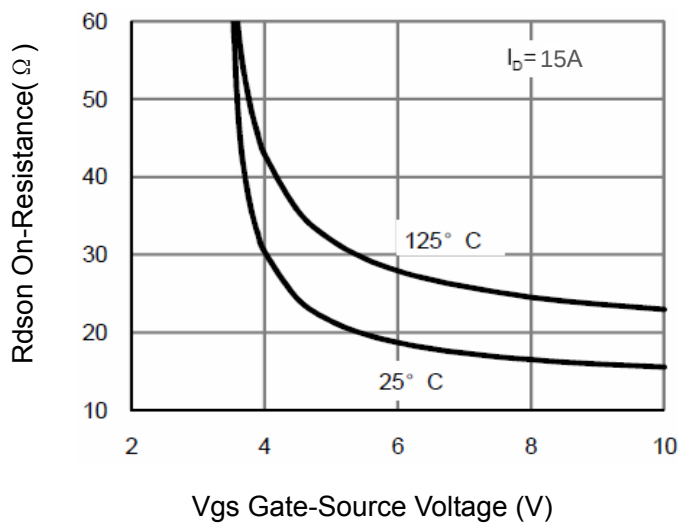


Figure 9 Rdson vs Vgs

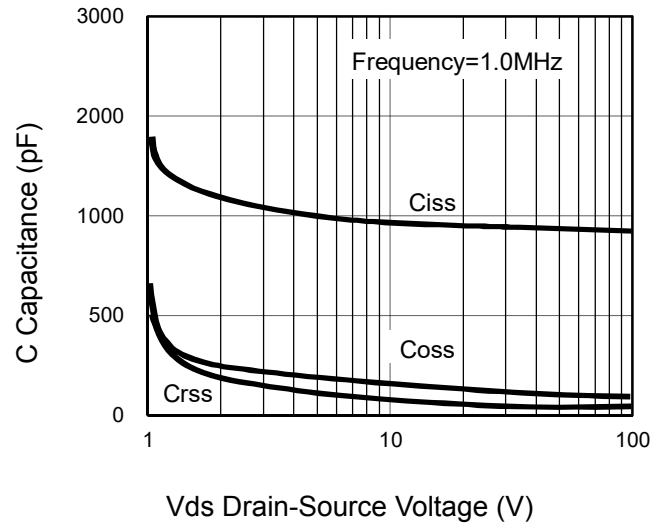


Figure 10 Capacitance vs Vds

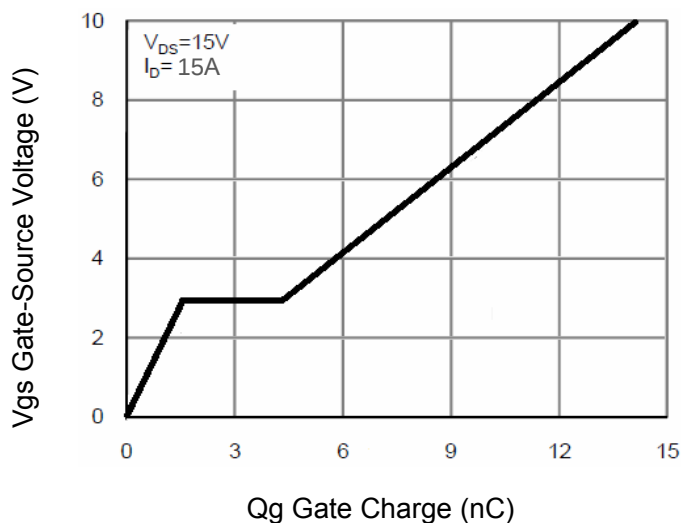


Figure 11 Gate Charge

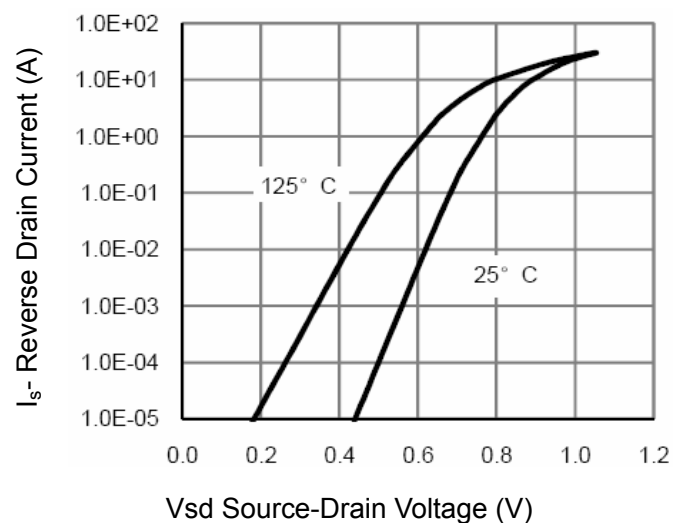


Figure 12 Source- Drain Diode Forward

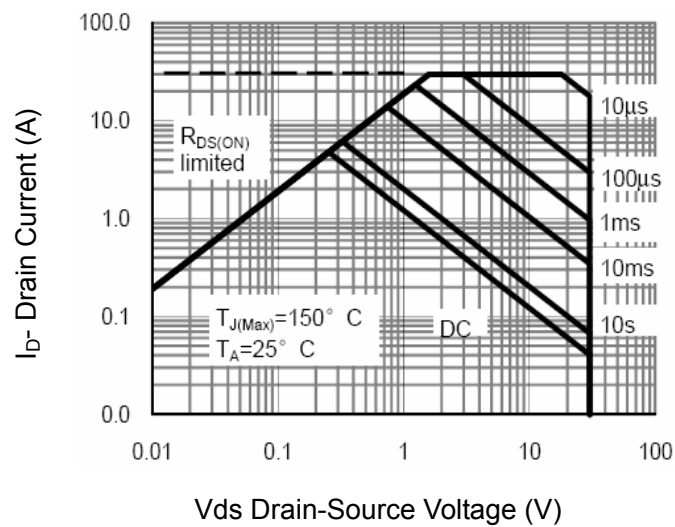


Figure 13 Safe Operation Area

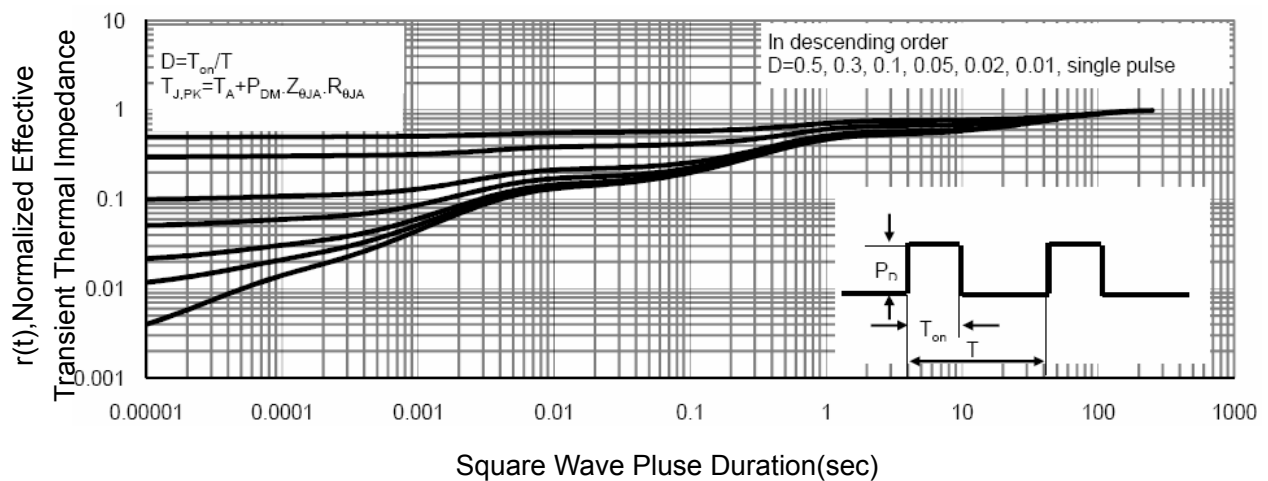
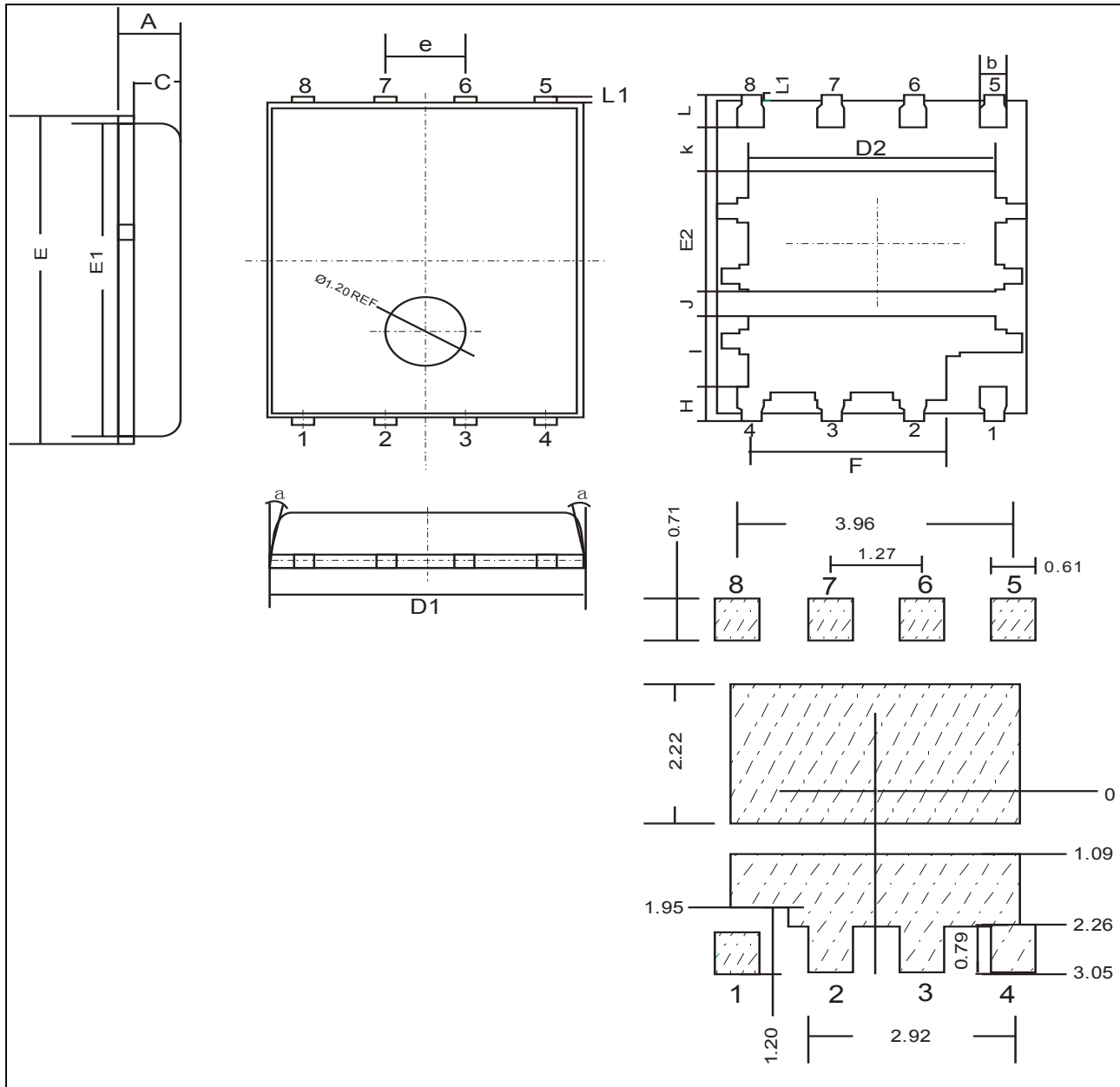


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN5060-8L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043	E1	5.70	5.75	5.80	0.224	0.226	0.228
b	0.33	0.41	0.51	0.013	0.016	0.020	E2	2.02	2.17	2.32	0.079	0.085	0.091
c	0.20	0.25	0.30	0.008	0.010	0.012	e	1.27BSC			0.05BSC		
D1	4.80	4.90	5.00	0.189	0.193	0.197	H	0.48	0.58	0.68	0.018	0.022	0.026
D2	3.61	3.81	3.96	0.142	0.150	0.156	L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008							
E	5.90	6.00	6.10	0.232	0.236	0.240	@	0°	*	12°	*	10°	12°
K	0.50	*	*	0.019	*	*	J	0.40	0.50	0.60	0.015	0.019	0.023
I	1.22	1.32	1.42	0.048	0.051	0.055	F	2.87	3.07	3.22	0.112	0.12	0.126